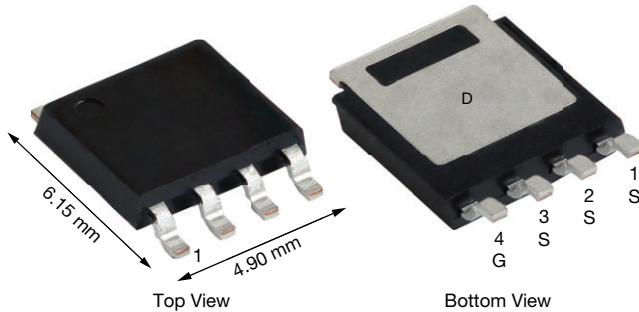




# Automotive N-Channel 80 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L



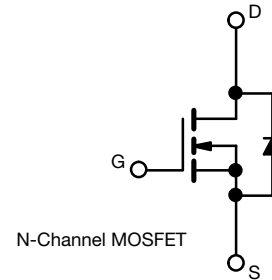
## FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>g</sub> and UIS tested
- Q<sub>gd</sub>/Q<sub>gs</sub> ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

AUTOMOTIVE GRADE



RoHS COMPLIANT HALOGEN FREE



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	80
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V	0.0030
I <sub>D</sub> (A)	248
Configuration	Single
Package	PowerPAK SO-8L

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-source voltage	V <sub>DS</sub>		80	V
Gate-source voltage	V <sub>GS</sub>		± 20	
Continuous drain current	T <sub>C</sub> = 25 °C		248	A
	T <sub>C</sub> = 125 °C		143	
Continuous source current (diode conduction)	I <sub>S</sub>		248	
Pulsed drain current	I <sub>DM</sub>		420	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	42	mJ
Single pulse avalanche energy		E <sub>AS</sub>	88	
Maximum power dissipation	T <sub>C</sub> = 25 °C		500	W
	T <sub>C</sub> = 125 °C		166	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>		-55 to +175	°C
Soldering recommendations (peak temperature) <sup>b</sup>			260	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL		LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>a</sup>		R <sub>thJA</sub>	°C/W
Junction-to-case (drain)			R <sub>thJC</sub>	

### Notes

- When mounted on 1" square PCB (FR4 material)
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



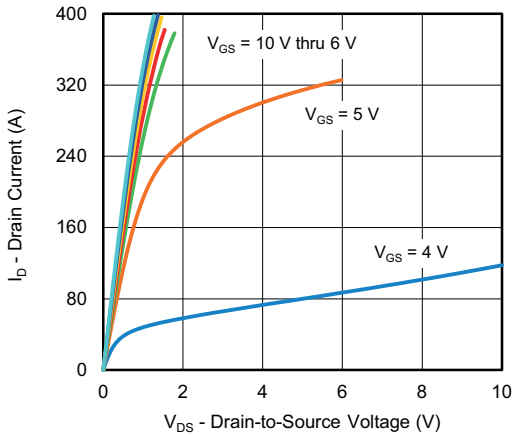
SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA	80	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.2	2.7	3.5	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 80 V	-	-	10	μA
		V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 80 V, T <sub>J</sub> = 125 °C	-	-	50	
		V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 80 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> ≥ 5 V	30	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	-	0.0025	0.0030	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.0059	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.0075	
Forward transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A	-	82	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz	-	4746	6645	pF
Output capacitance	C <sub>oss</sub>		-	814	1140	
Reverse transfer capacitance	C <sub>rss</sub>		-	51	72	
Total gate charge <sup>c</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 40 V, I <sub>D</sub> = 10 A	-	78	117	nC
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>		-	18	-	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>		-	16	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.5	1.0	1.50	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 40 V, R <sub>L</sub> = 4 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	16	20	ns
Rise time <sup>c</sup>	t <sub>r</sub>		-	10	15	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>		-	39	50	
Fall time <sup>c</sup>	t <sub>f</sub>		-	9	15	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>		-	-	420	A
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V	-	-	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs	-	50	65	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	71	95	nC
Reverse recovery fall time	t <sub>a</sub>		-	28	44	ns
Reverse recovery rise time	t <sub>b</sub>		-	22	38	
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	2.4	3.6

**Notes**

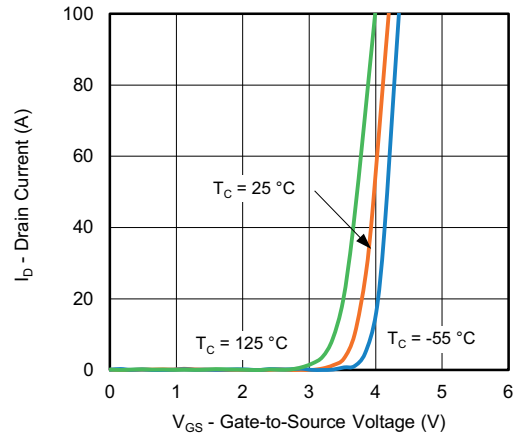
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %  
b. Guaranteed by design, not subject to production testing  
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

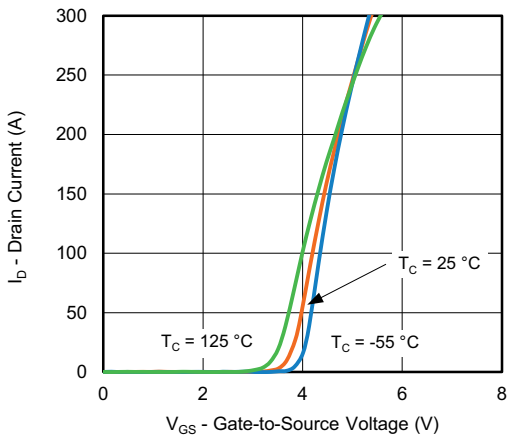
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



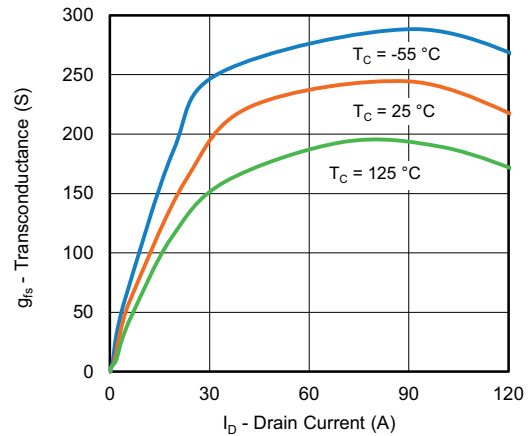
**Output Characteristics**



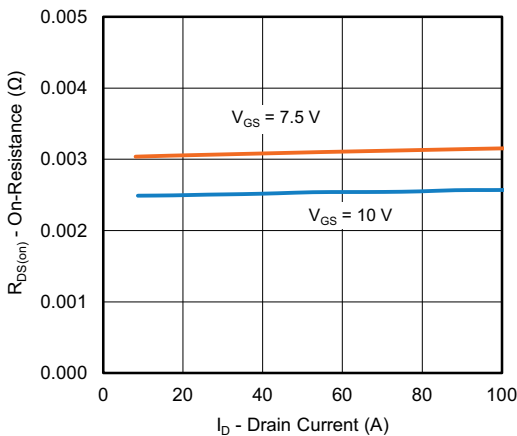
**Transfer Characteristics**



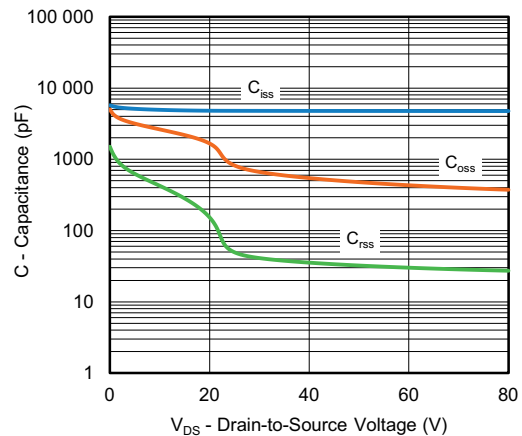
**Transfer Characteristics**



**Transconductance**



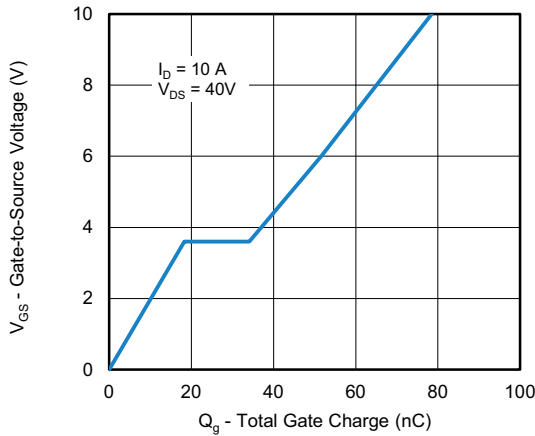
**On-Resistance vs. Drain Current**



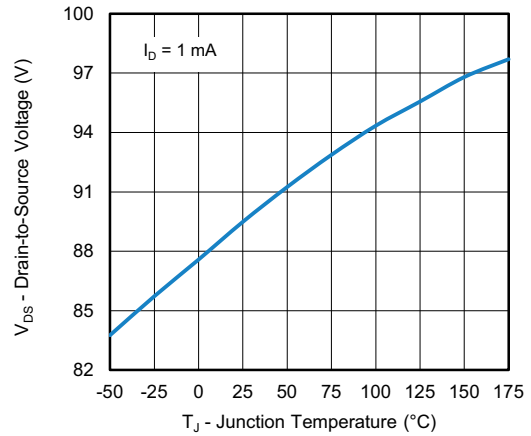
**Capacitance**



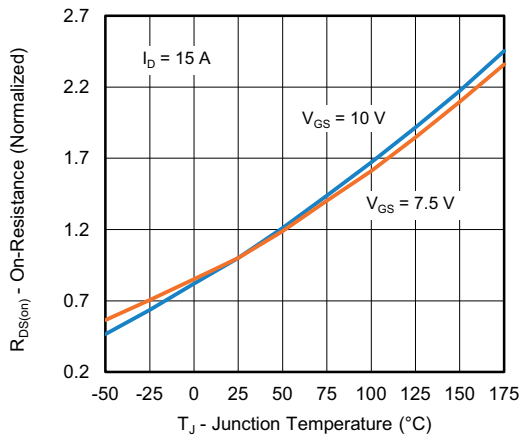
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



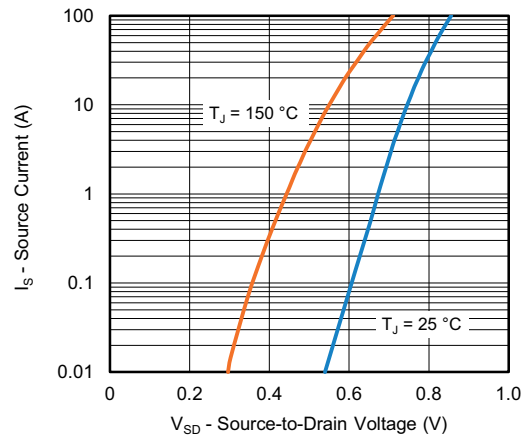
Gate Charge



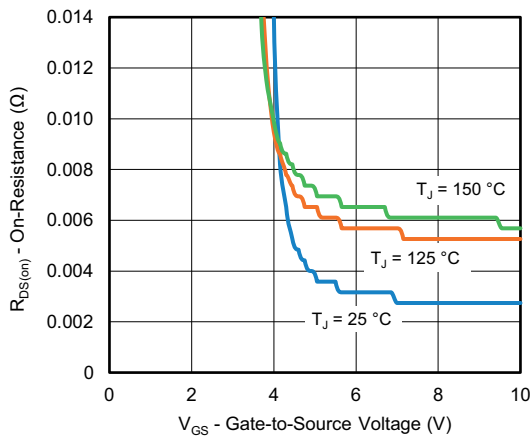
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Junction Temperature



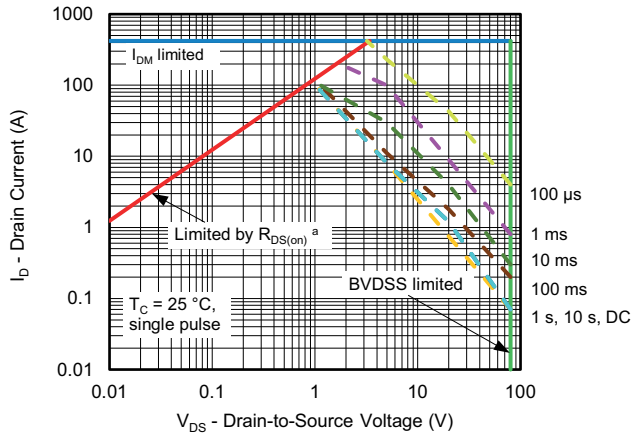
Source Drain Diode Forward Voltage



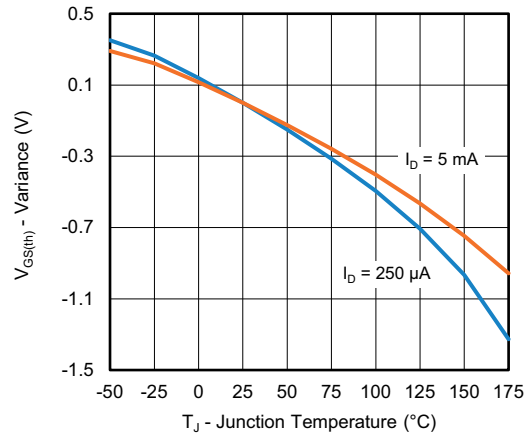
On-Resistance vs. Gate to Source Voltage



**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Safe Operating Area**

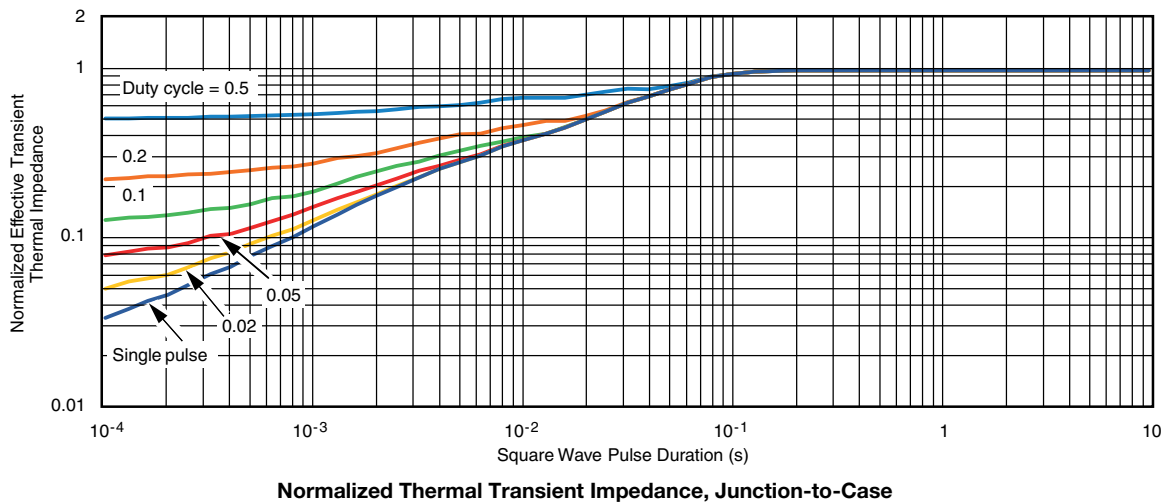
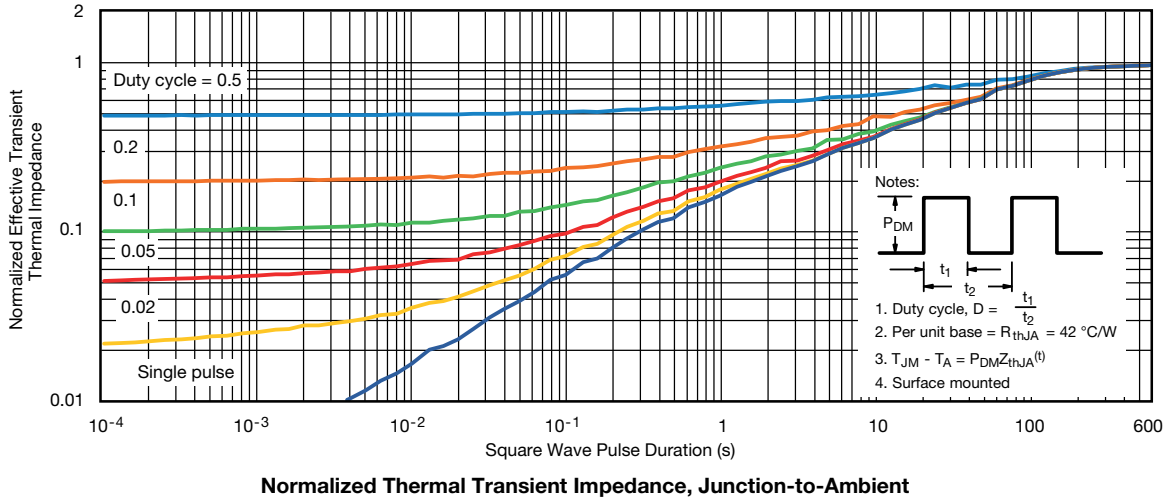


**Threshold Voltage**

**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

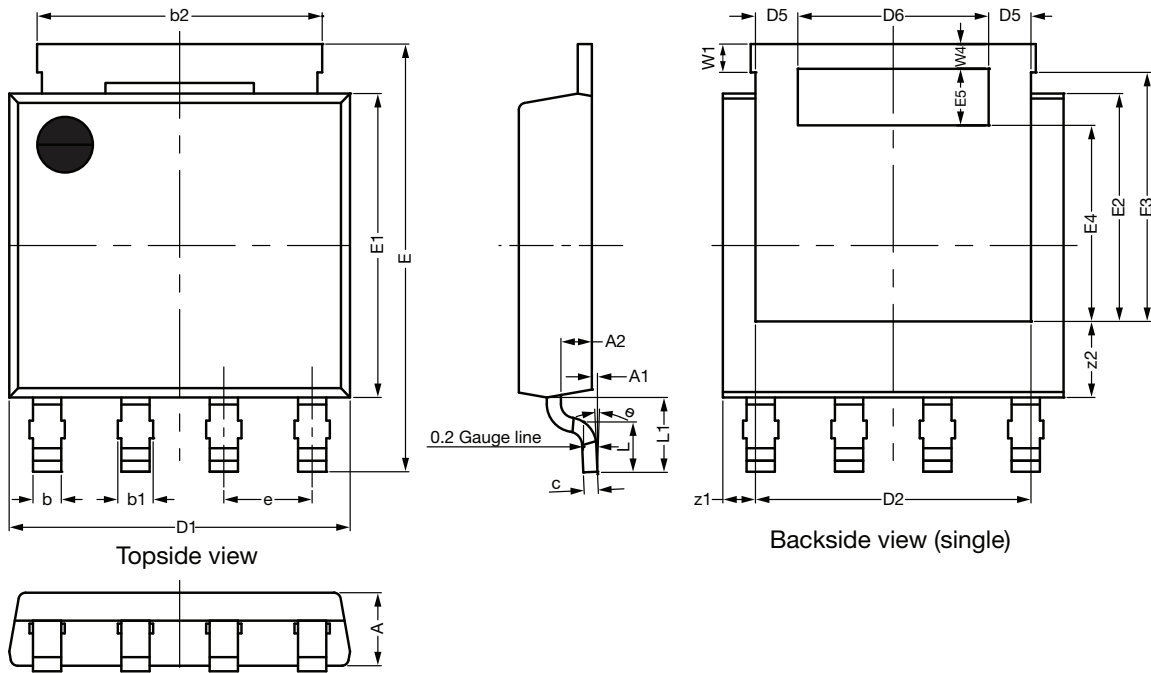


**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^\circ\text{C}$ )
  - Normalized Transient Thermal Impedance Junction-to-Case ( $25\text{ }^\circ\text{C}$ )
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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### PowerPAK<sup>®</sup> SO-8L Case Outline 3



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.05	1.10	0.039	0.041	0.043
A1	0.00	---	0.127	0.000	---	0.005
A2	0.40	0.45	0.50	0.016	0.018	0.020
b	0.33	0.41	0.49	0.013	0.016	0.019
b1	0.43	0.51	0.59	0.017	0.020	0.023
b2	4.00	4.10	4.20	0.157	0.161	0.165
c	0.15	0.20	0.25	0.006	0.008	0.010
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D5	0.51	0.61	0.71	0.020	0.024	0.028
D6	2.64	2.74	2.84	0.104	0.108	0.112
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
E3	3.48	3.58	3.68	0.137	0.141	0.145
E4	2.72	2.82	2.92	0.107	0.111	0.115
E5	0.71	0.81	0.91	0.028	0.032	0.036
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
W1	0.31	0.41	0.51	0.012	0.016	0.020
W4	0.31	0.36	0.41	0.012	0.014	0.016
z1	0.37	0.47	0.57	0.015	0.019	0.022
z2	0.99	1.09	1.19	0.039	0.043	0.047
θ	0°	---	5°	0°	---	5°

ECN: S19-0643-Rev. B, 05-Aug-2019

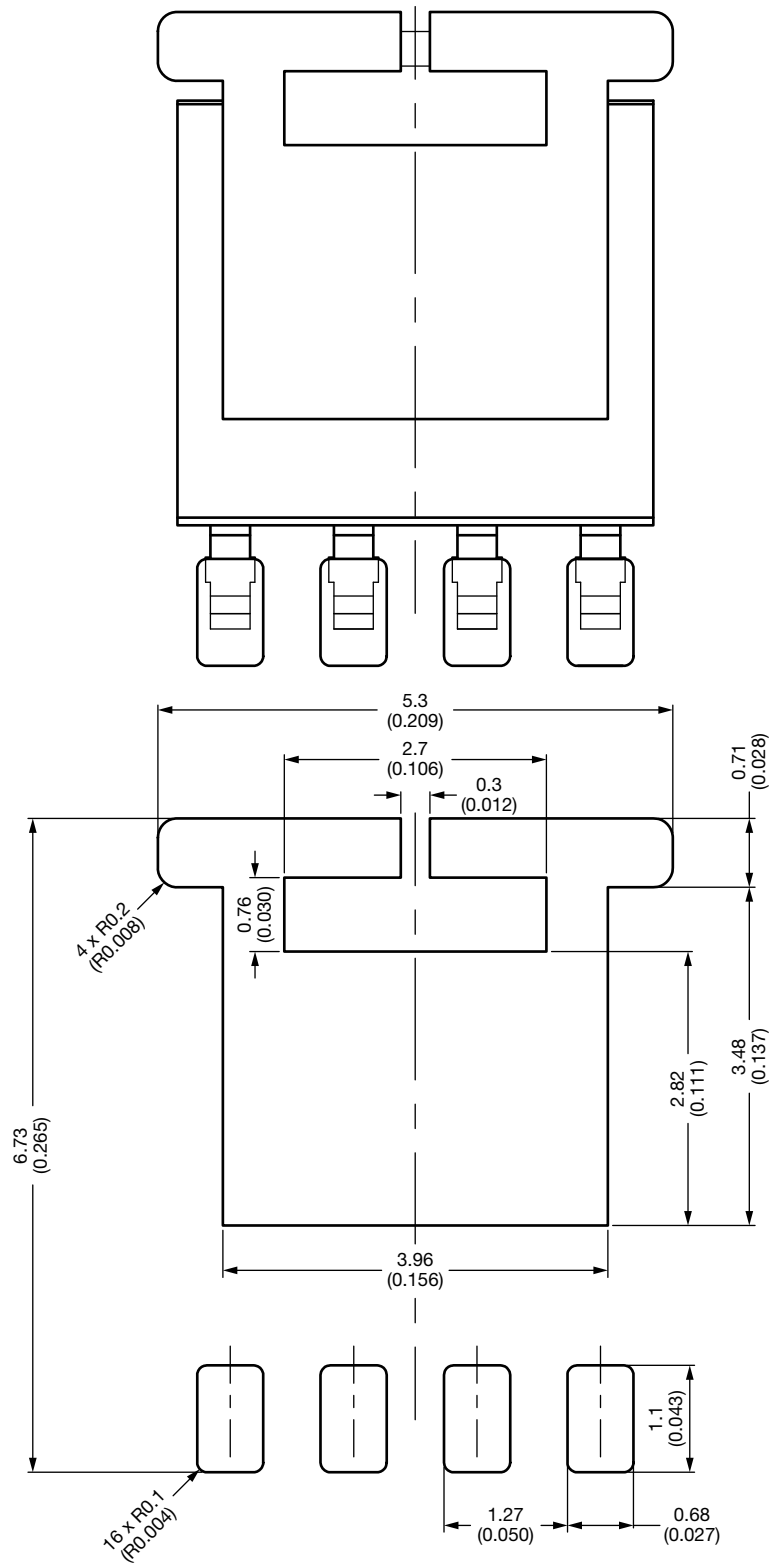
DWG: 6067

**Note**

- Millimeter will govern



# Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)





## Disclaimer

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